

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re application of:

Yoshiki Sakuma et al

Serial No.: 09/819,762

Filed: March 29, 2001

For: HETEROBIPOLAR TRANSISTOR AND A METHOD OF FORMING A SiGeC MIXED CRYSTAL LAYER



Group Art Unit: 2812

Examiner: Christopher W. Lattin

#5/Elect.
3/15/02
V. Vannall

RESPONSE TO RESTRICTION REQUIREMENT

Commissioner for Patents
Washington, D.C. 20231

March 12, 2002

Sir:

This is in response to the Office Action of February 12, 2002, requiring restriction between two alleged inventions under the provisions of 35 USC § 121.

In the Action, the examiner has made a restriction requirement between the inventions of Group I drawn to a heterobipolar transistor (claims 1-13) and Group II drawn to method supplying source gases (claims 14-18).

Applicants hereby provisionally elect **Group I, that is, claims 1-13** for examination on the merits in this application. Applicants reserve the right to file one or more divisional applications directed to the subject matter of the non-elected claims.

Favorable consideration of the subject application is respectfully requested.

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In the event this paper is not timely filed, the undersigned hereby petitions for an appropriate extension of time. The fee for this extension may be charged to Deposit Account No. 01-2340, along with any other additional fees which may be required with respect to this response.

Respectfully submitted,

ARMSTRONG, WESTERMAN & HATTORI, LLP

A handwritten signature in black ink, appearing to read 'Donald W. Hanson', written over a horizontal line.

Donald W. Hanson
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